

General Description

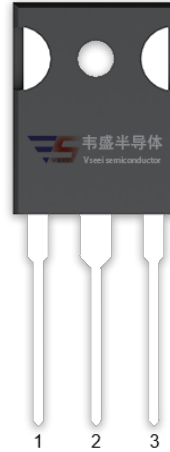
The series of devices use advanced super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

Features

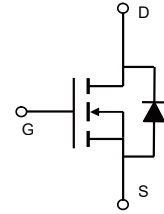
- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)



TO-247



Schematic

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	650	V
Gate-Source Voltage ($V_{DS}=0V$) AC ($f>1$ Hz)	V_{GS}	± 30	V
Continuous Drain Current at $T_c=25^\circ C$	$I_D (DC)$	75	A
Continuous Drain Current at $T_c=100^\circ C$	$I_D (DC)$	47	A
Pulsed drain current (Note 1)	$I_{DM} (pulse)$	300	A
Maximum Power Dissipation($T_c=25^\circ C$)	P_D	510	W
Derate above $25^\circ C$		4.08	W/ $^\circ C$
Single pulse avalanche energy (Note 2)	EAS	1936	mJ
Avalanche current (Note 1)	I_{AR}	28	A
Repetitive Avalanche energy , t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	2.5	mJ

Parameter	Symbol	Value	Unit
Drain Source voltage slope, $V_{DS} \leq 480V$,	dv/dt	50	V/ns
Reverse diode dv/dt , $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+150	°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	0.245	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	°C /W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =500μA	650			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =650V,V _{GS} =0V			5	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =650V,V _{GS} =0V			500	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =500μA	2.5	3.5	4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =38A		36	41	mΩ
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =100V,V _{GS} =0V, F=1.0MHz		7300	8500	PF
Output Capacitance	C _{oss}			252		PF
Reverse Transfer Capacitance	C _{rss}			4		PF
Total Gate Charge	Q _g	V _{DS} =480V,I _D =75A, V _{GS} =10V		116	135	nC
Gate-Source Charge	Q _{gs}			40		nC
Gate-Drain Charge	Q _{gd}			30		nC
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =380V,I _D =38A, R _G =1.2Ω,V _{GS} =10V		27		nS
Turn-on Rise Time	t _r			22		nS
Turn-Off Delay Time	t _{d(off)}			118	180	nS
Turn-Off Fall Time	t _f			13	30	nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃		75		A
Pulsed Source-drain current(Body Diode)	I _{SDM}			300		A
Forward on voltage	V _{SD}	T _j =25℃,I _{SD} =75A,V _{GS} =0V		1.3		V
Reverse Recovery Time	t _{rr}	T _j =25℃,I _F =38A,di/dt=100A/μs V _{DD} =300V		230		nS
Reverse Recovery Charge	Q _{rr}			3		uC
Peak Reverse Recovery Current	I _{rrm}			26		A

Notes 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

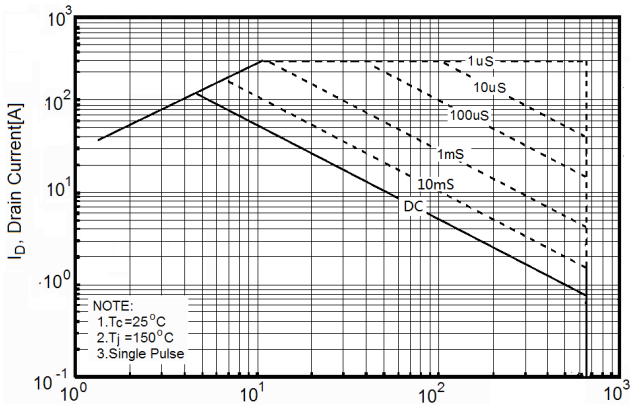
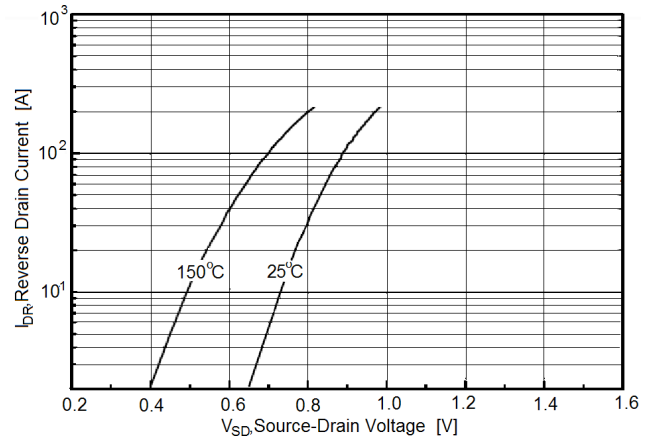
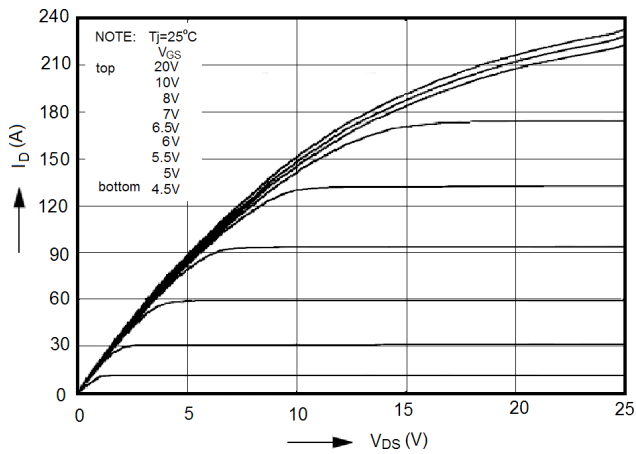
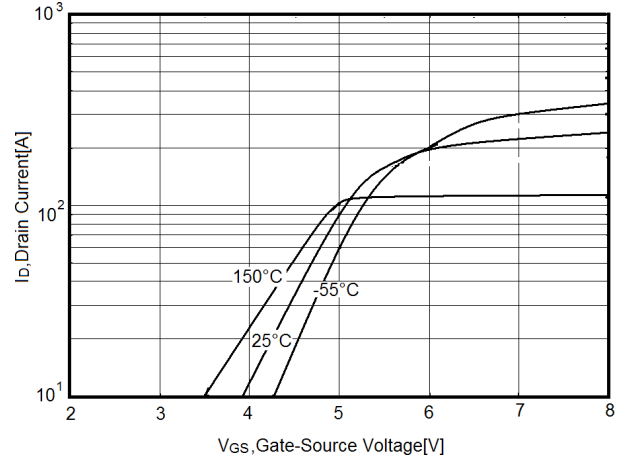
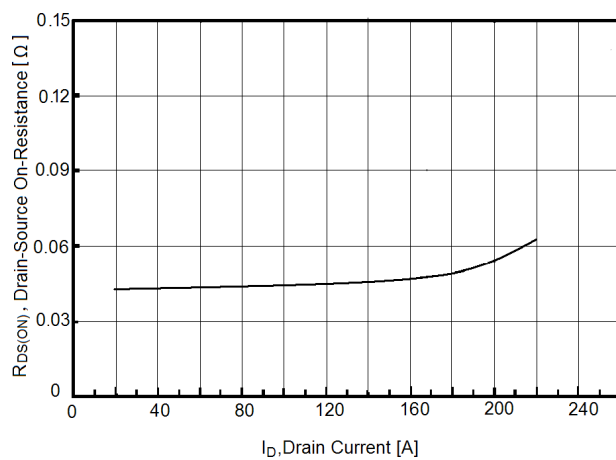
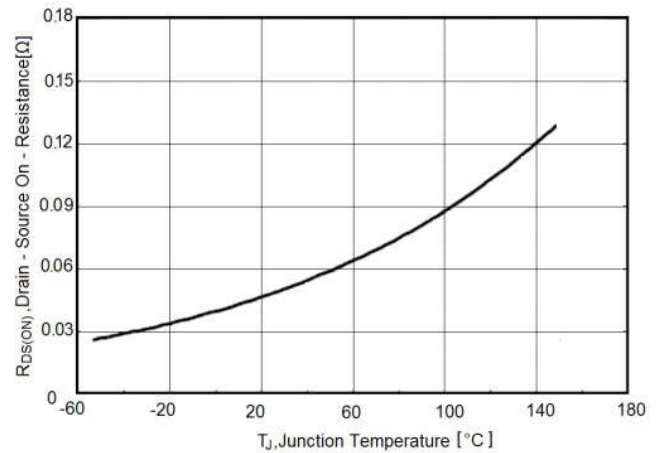
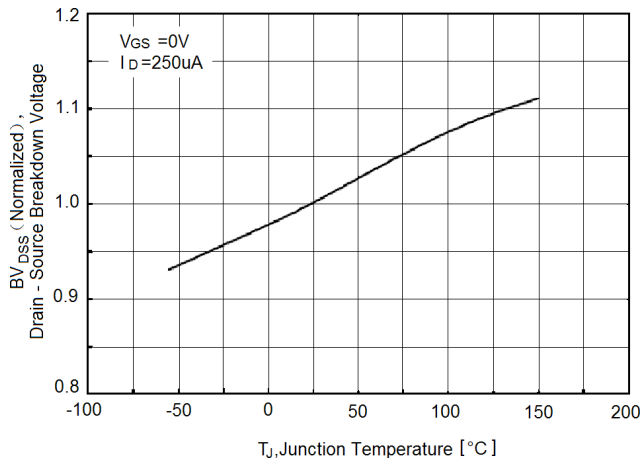
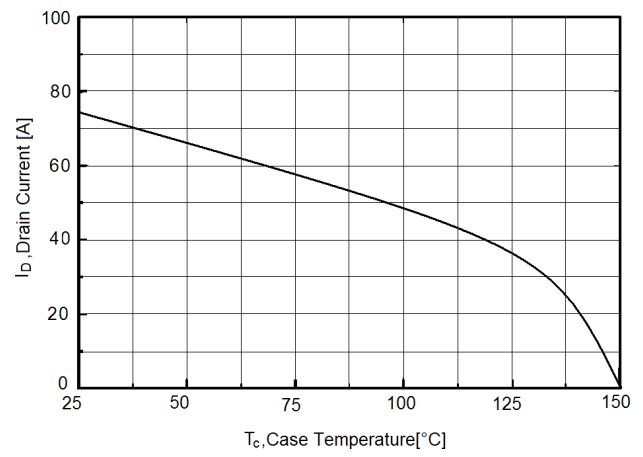
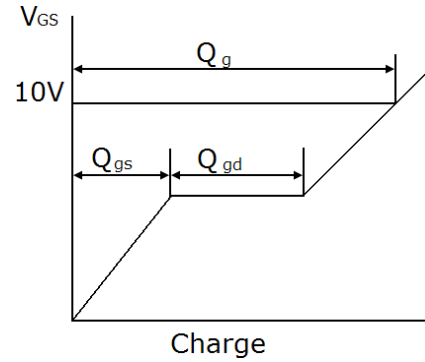
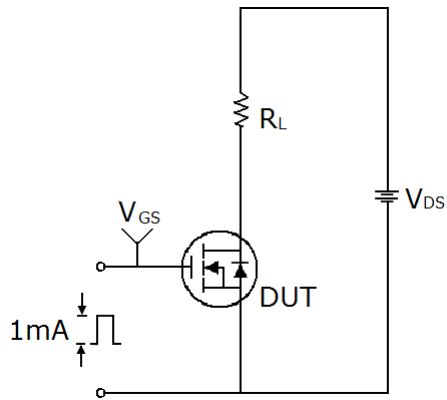
Figure1. Safe Operating Area

Figure3. Source-Drain Diode Forward Voltage

Figure4. Output Characteristics

Figure5. Transfer Characteristics

Figure6. Static drain-source on resistance

Figure7. $R_{DS(ON)}$ vs Junction Temperature


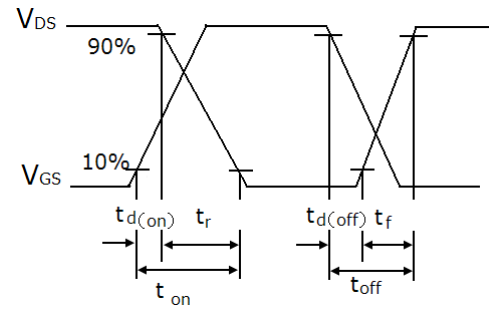
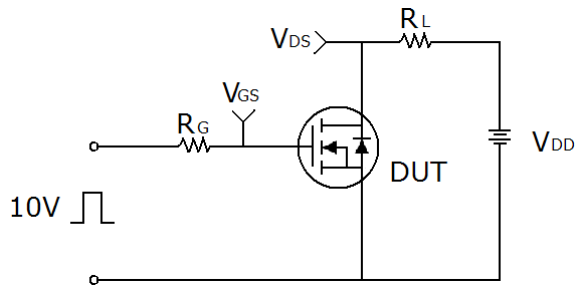
Figure8. BV_{DSS} vs Junction Temperature

Figure9. Maximum I_D vs Junction Temperature


Test circuit

1) Gate charge test circuit & Waveform



2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

